

SILICON SCHOTTKY BARRIER DETECTOR DIODES

Description

Silicon Schottky barrier detector diodes are available as:

- packaged diodes
- chip

They are optimized for wide band applications, in the frequency range from 1 to 18 GHz.

Electrical characteristics packaged diodes

Characteristics at 25°C		Frequency range F_{oper}	Tangential sensitivity T_{SS}	Video resistance R_V		RF power P_{RF}	Forward continuous current I_F	Breakdown voltage V_{BR}
Test conditions		N/A	Video bandwidth = 1 MHz $I_F = 30 \mu A$			CW	N/A	$I_R = 10 \mu A$
TYPE	CASE (1)	GHz	dBm	k Ω		mW	mA	V
			min.	min.	max	max	max	typ.
DH340	F51	2 - 12	- 54	1	2	250	50	3
		12 - 18	- 51					

(1) Custom cases available on request

Temperature ranges:

Operating junction (T_j) : -55° C to +150° C

Storage : -65° C to +175° C

- $T = + 25^\circ C$
- $I_F = 30 \mu A$
- Video bandwidth = 1 MHz

Typical tangential sensitivity vs frequency

